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(54) Title: DEVICES FORMED FROM A NON-POLAR PLANE OF A CRYSTALLINE MATERIAL AND METHOD OF MAKING THE SAME

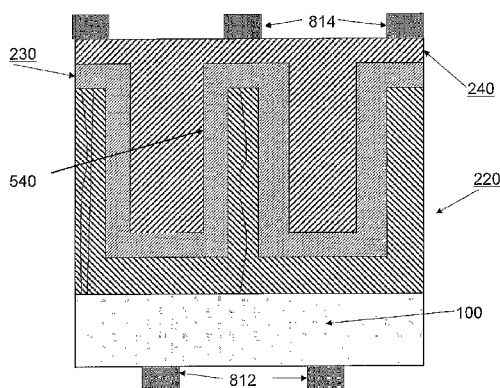


FIGURE 8

(57) Abstract: Materials, methods, structures and device including the same can provide a semiconductor device such as an LED using an active region corresponding to a non-polar face or surface of III-V semiconductor crystalline material. In some embodiments, an active diode region contains more non-polar III-V material oriented to a non-polar plane than III-V material oriented to a polar plane. In other embodiments, a bottom region contains more non-polar m-plane or a-plane surface area GaN than polar c-plane surface area GaN facing an active region.